



# ACE12341B

## P-Channel Enhancement Mode Field Effect Transistor

### Description

Load switch for Portable Applications.

### Features

- $V_{DS}=-20V$
- $I_D=-2A$
- $R_{DS(ON)} @ V_{GS}=-4.5V, TYP 100m\Omega$
- $R_{DS(ON)} @ V_{GS}=-2.5V, TYP 120m\Omega$

### Absolute Maximum Ratings

Parameter		Symbol	Max	Unit
Drain-Source Voltage		$V_{DSS}$	-20	V
Gate-Source Voltage		$V_{GSS}$	$\pm 12$	V
Drain Current (Continuous)*AC	$T_A=25^\circ C$	$I_D$	-2	A
	$T_A=70^\circ C$		-1.4	
Drain Current (Pulsed)*B		$I_{DM}$	-10	A
Power Dissipation	$T_A=25^\circ C$	$P_D$	1.25	W
Operating temperature / storage temperature		$T_J/T_{STG}$	-55~150	$^\circ C$

Note :

- The value of  $R_{\theta JA}$  is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ C$ . The value in any given application depends on the user's specific board design.
- Repetitive rating, pulse width limited by junction temperature.
- The current rating is based on the  $t \leq 10s$  junction to ambient thermal resistance rating.

### Thermal Resistance Ratings

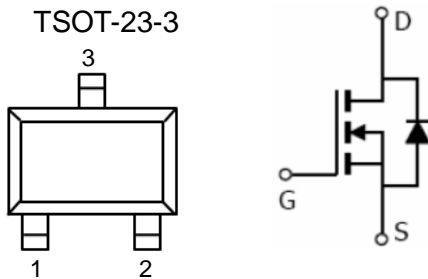
Parameter		Symbol	Typical	Max	Unit
Maximum Junction-to-Ambient	$t \leq 5s$	$R_{thJA}$	80	100	$^\circ C/W$



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### Packaging Type

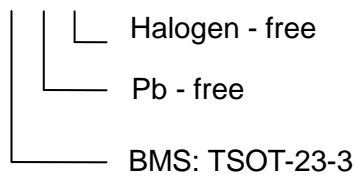


### Pin Configuration

TSOT-23-3	Description	Function
1	G	Gate
2	S	Source
3	D	Drain

### Ordering information

ACE12341B XX + H





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### Electrical Characteristics

T<sub>A</sub>=25°C, unless otherwise specified.

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	-20			V
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> =-20V, V <sub>GS</sub> =0V			-1	μA
Gate threshold voltage	V <sub>GS(th)</sub>	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>DS</sub> =250μA	-0.4	-0.7	-1.2	V
Gate leakage current	I <sub>GSS</sub>	V <sub>GS</sub> =±12V, V <sub>DS</sub> =0V			±100	nA
Drain-Source On-state Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-2A		100	150	mΩ
		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-1A		120	200	
Forward trans conductance	g <sub>FS</sub>	V <sub>DS</sub> =-5V, I <sub>D</sub> =-2A		6.5		S
Diode forward voltage	V <sub>SD</sub>	I <sub>SD</sub> =-1A, V <sub>GS</sub> =0V			-1.2	V
Diode forward current	I <sub>S</sub>	TC =25°C			-2	A
Switching						
Total gate charge	Q <sub>g</sub>	V <sub>GS</sub> =-4.5V, V <sub>DS</sub> =-10V, I <sub>D</sub> =-2A		3.8		nC
Gate-source charge	Q <sub>gs</sub>			0.7		
Gate-drain charge	Q <sub>gd</sub>			0.5		
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> =-10V, I <sub>D</sub> =-2A R <sub>G</sub> =3Ω, V <sub>GS</sub> =-4.5V		15		ns
Turn-on rise time	Tr			17		
Turn-off delay time	t <sub>d(off)</sub>			24		
Turn-off fall time	Tf			8		
Dynamic						
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =-10V, f=1.0MHz		400		pF
Output capacitance	C <sub>oss</sub>			90		
Reverse transfer capacitance	C <sub>rss</sub>			60		



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### Typical Performance Characteristics

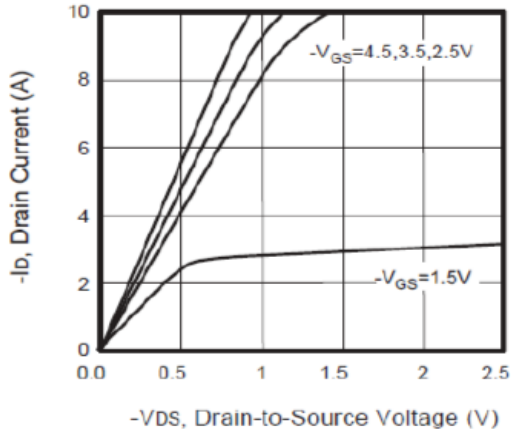


Figure 1. Output Characteristics

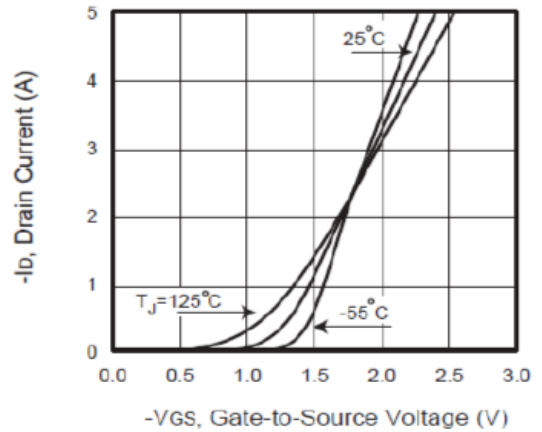


Figure 2. Transfer Characteristics

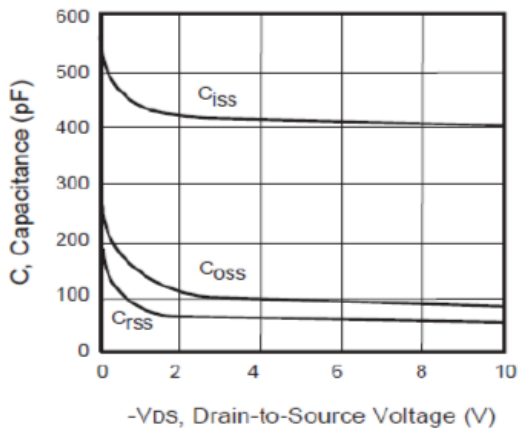


Figure 3. Capacitance

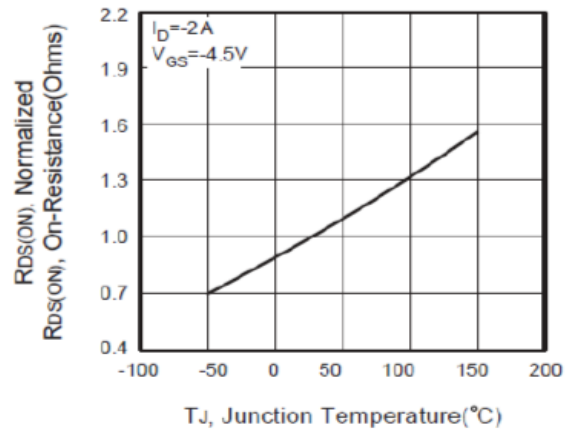


Figure 4. On-Resistance Variation with Temperature

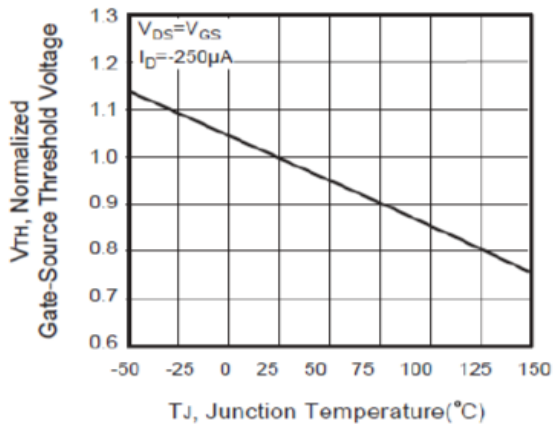


Figure 5. Gate Threshold Variation with Temperature

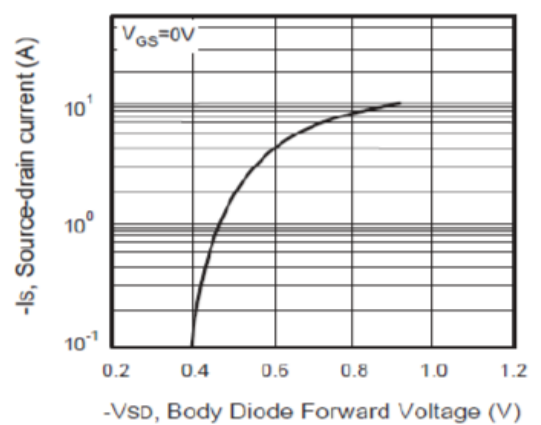


Figure 6. Body Diode Forward Voltage Variation with Source Current



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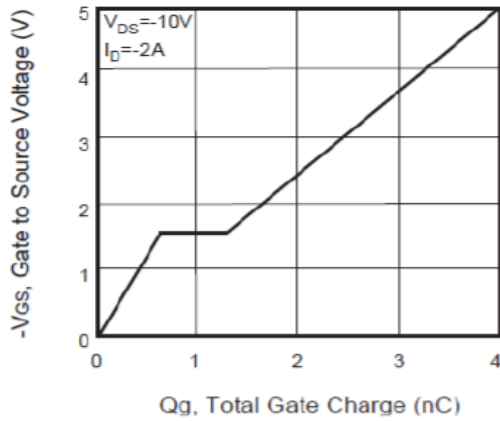


Figure 7. Gate Charge

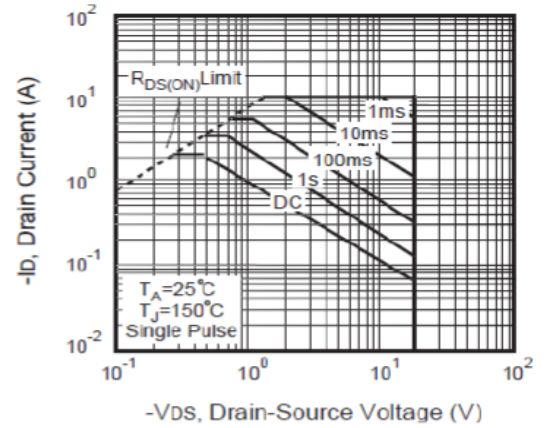


Figure 8. Maximum Safe Operating Area

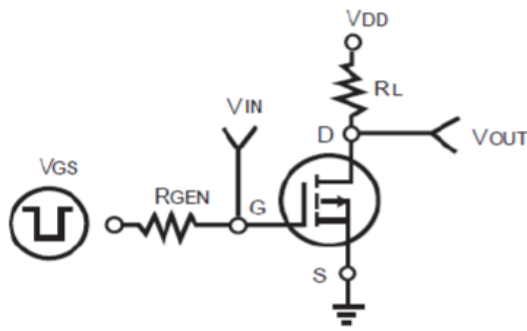


Figure 9. Switching Test Circuit

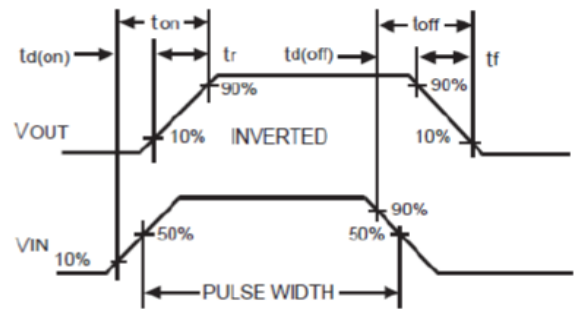


Figure 10. Switching Waveforms

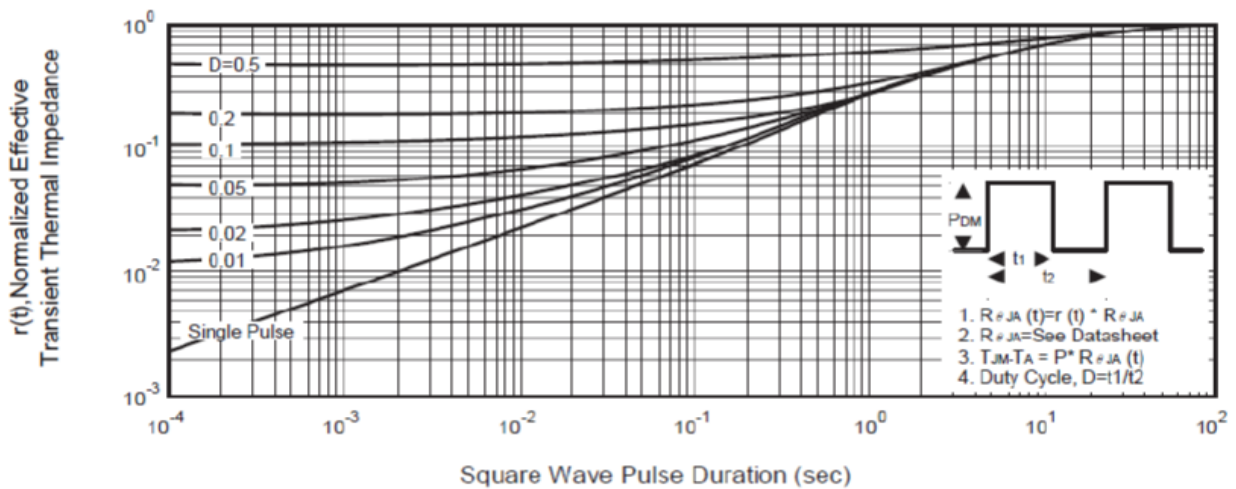


Figure 11. Normalized Thermal Transient Impedance Curve

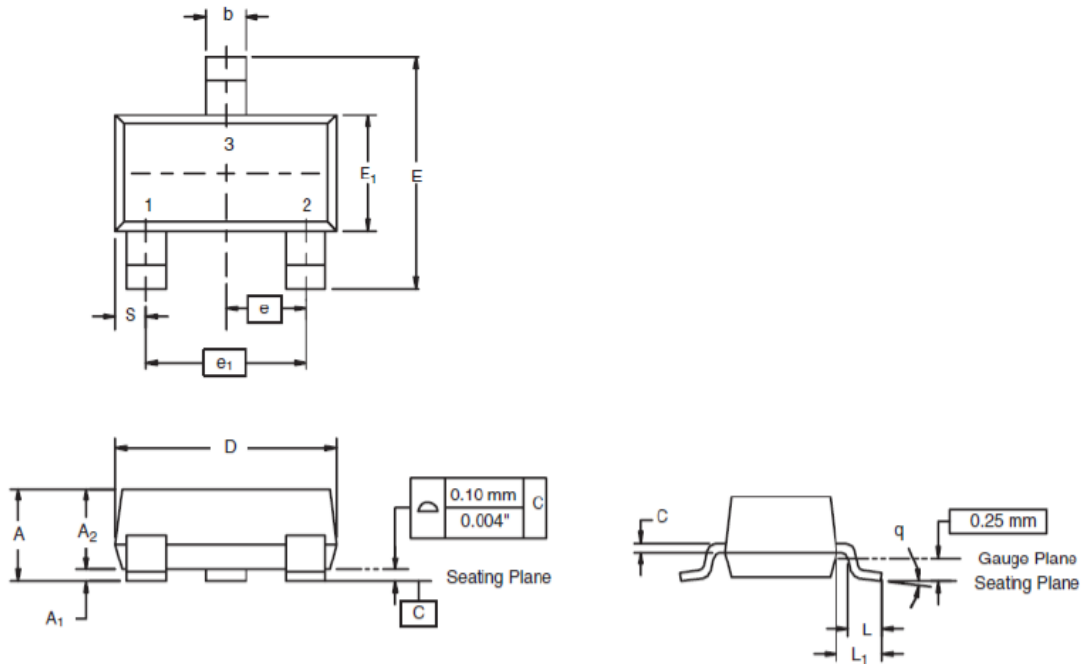


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### Packing Information

TSOT-23-3



Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	0.89	1.12	0.035	0.044
A <sub>1</sub>	0.01	0.10	0.0004	0.004
A <sub>2</sub>	0.88	1.02	0.0346	0.040
b	0.35	0.50	0.014	0.020
c	0.085	0.18	0.003	0.007
D	2.80	3.04	0.110	0.120
E	2.10	2.64	0.083	0.104
E <sub>1</sub>	1.20	1.40	0.047	0.055
e	0.95 BSC		0.0374 Ref	
e <sub>1</sub>	1.90 BSC		0.0748 Ref	
L	0.40	0.60	0.016	0.024
L <sub>1</sub>	0.64 Ref		0.025 Ref	
S	0.50 Ref		0.020 Ref	
q	3°	8°	3°	8°



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### Notes

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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